

Low Temperature Aluminium Nitride Deposition: Comparing Hydrazine and Ammonia

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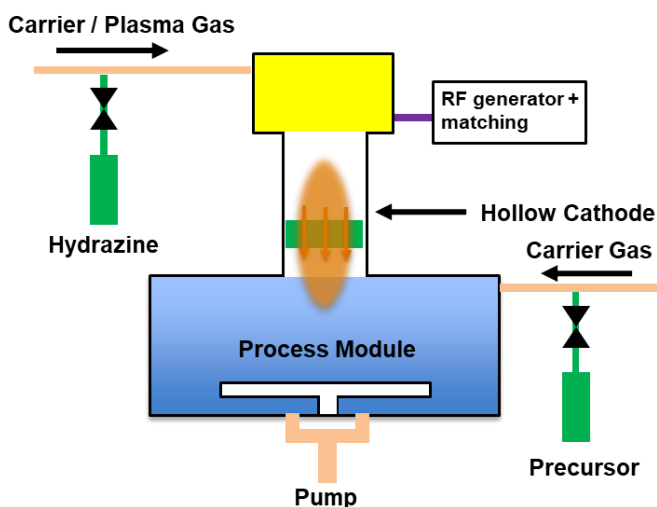


Figure 1. Schematic of the ALD reactor

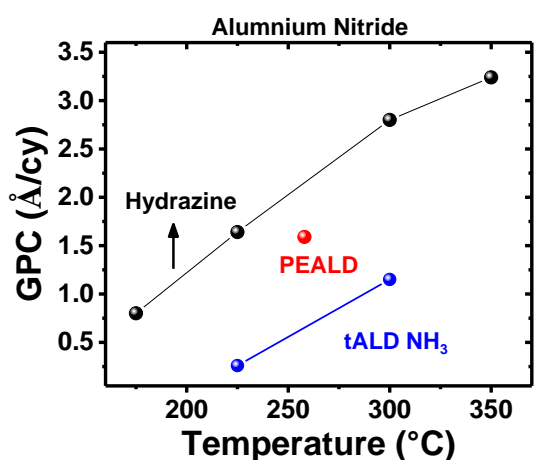


Figure 2. GPC comparison between different processes

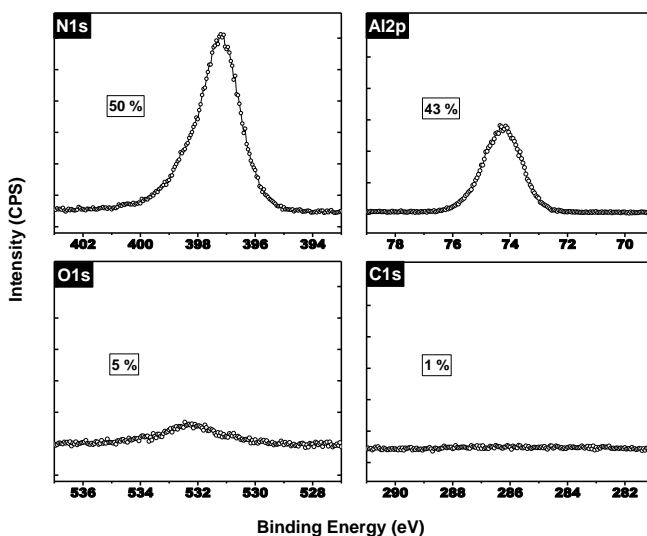


Figure 3. XPS elemental scans for Al_xN film deposited at 300 °C by t-ALD with hydrazine